

1. General description

Planar passivated very sensitive gate four quadrant triac in a TO220 plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- General purpose motor controls
- General purpose switching

4. Quick reference data

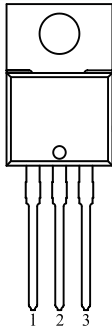
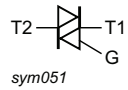
Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{DRM}	repetitive peak off-state voltage		600			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	4			A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	25			A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	27			A
T_j	junction temperature		125			°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	2	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	2.5	5	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2\text{- G-}; T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	2.5	5	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2\text{- G+}; T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	5	10	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9	-	1.2	10	mA
V_T	on-state voltage	$I_T = 5\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10	-	1.4	1.7	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 125\text{ }^\circ\text{C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$	-	5	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT136-600D	TO220	BT136-600D,127	Tube	50	TO220E	26-April-2019

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT136-600D	BT136-600D

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107\text{ }^{\circ}\text{C}$; Fig 1 ; Fig 2 ; Fig 3	4	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig 4 ; Fig 5	25	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	27	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	3.1	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 10\text{ mA}$; T2+ G+	50	$\text{A}/\mu\text{s}$
		$I_G = 10\text{ mA}$; T2+ G-	50	$\text{A}/\mu\text{s}$
		$I_G = 10\text{ mA}$; T2- G-	50	$\text{A}/\mu\text{s}$
		$I_G = 20\text{ mA}$; T2- G+	10	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_j	junction temperature		125	$^{\circ}\text{C}$

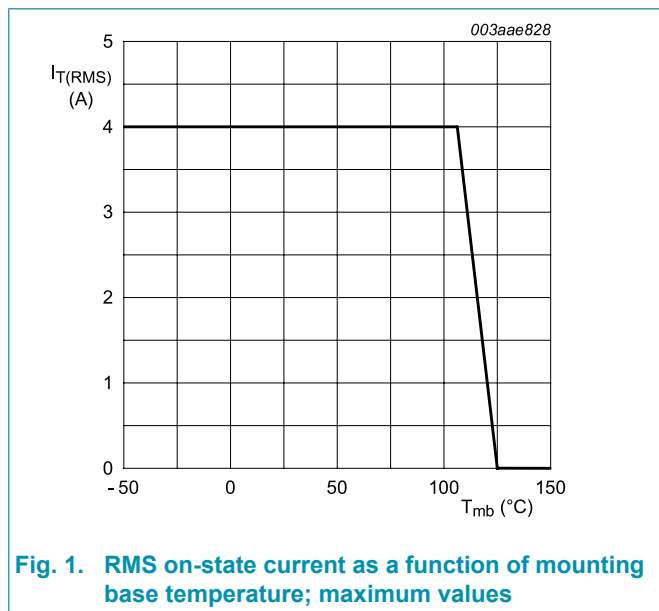


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

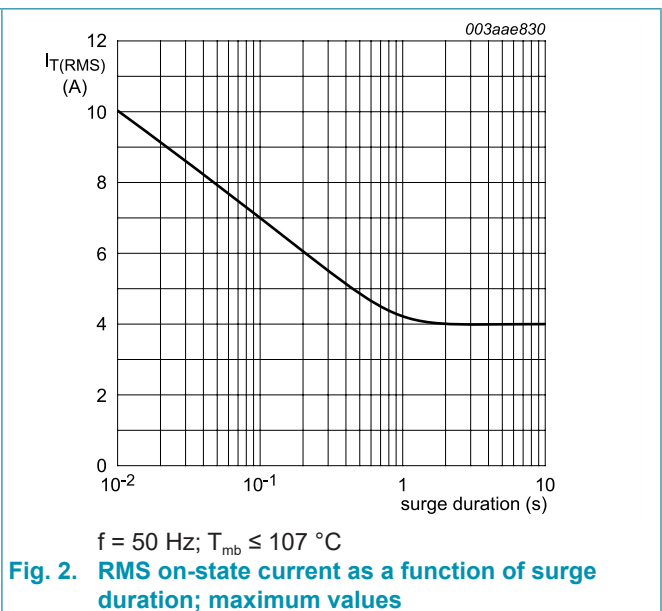
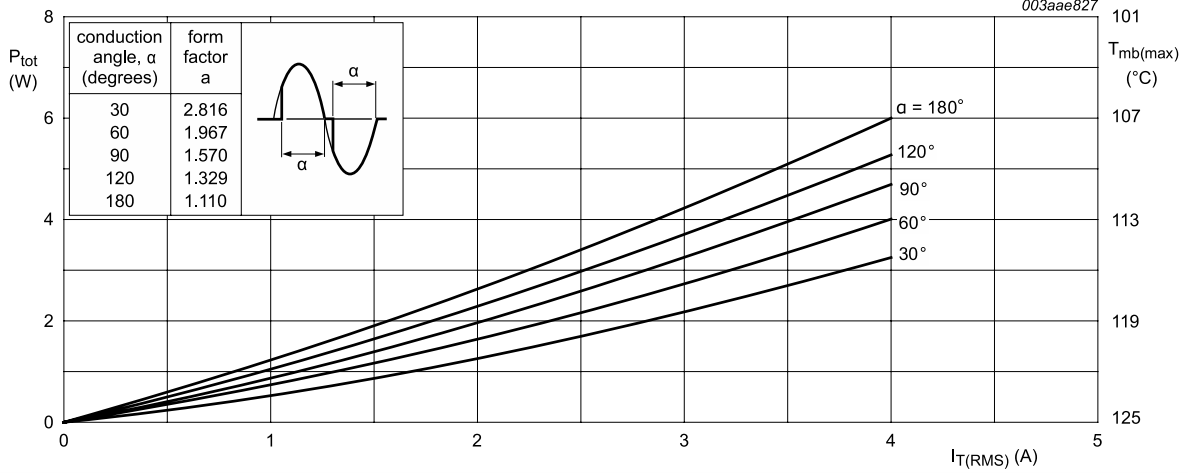
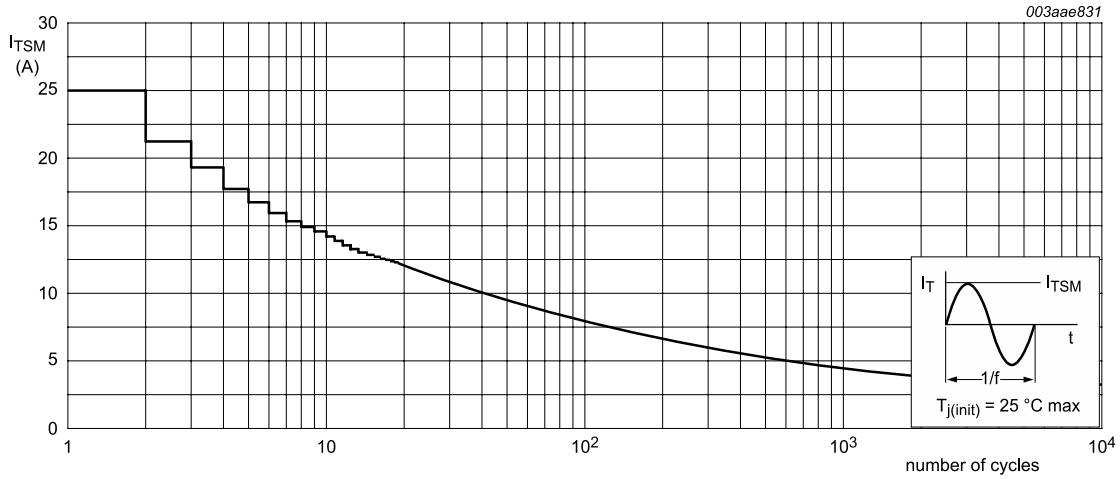


Fig. 2. RMS on-state current as a function of surge duration; maximum values
f = 50 Hz; $T_{mb} \leq 107\text{ }^{\circ}\text{C}$



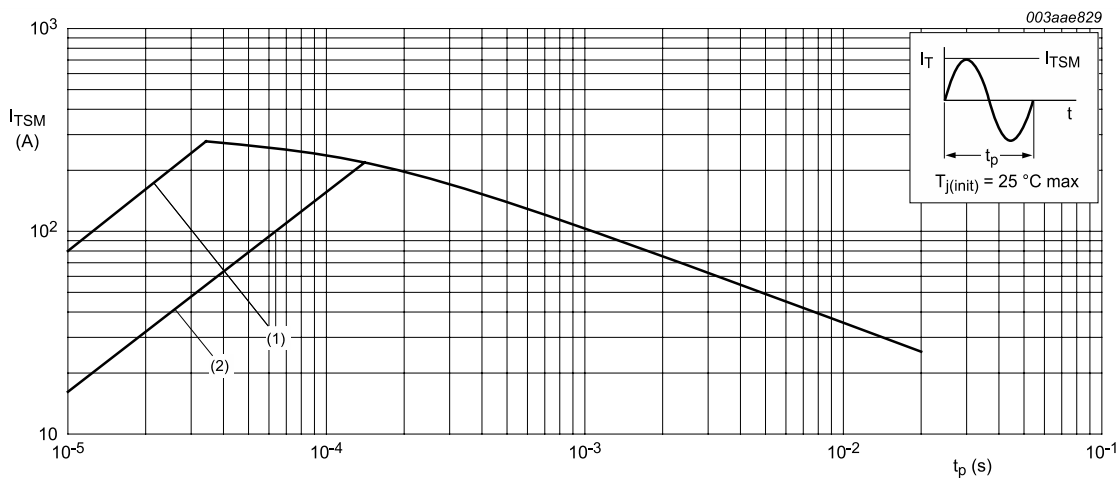
α = conduction angle
 a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$f = 50 \text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20 \text{ ms}$
 (1) di_T/dt limit
 (2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig 6	-	-	3	K/W
		half cycle; Fig 6	-	-	3.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

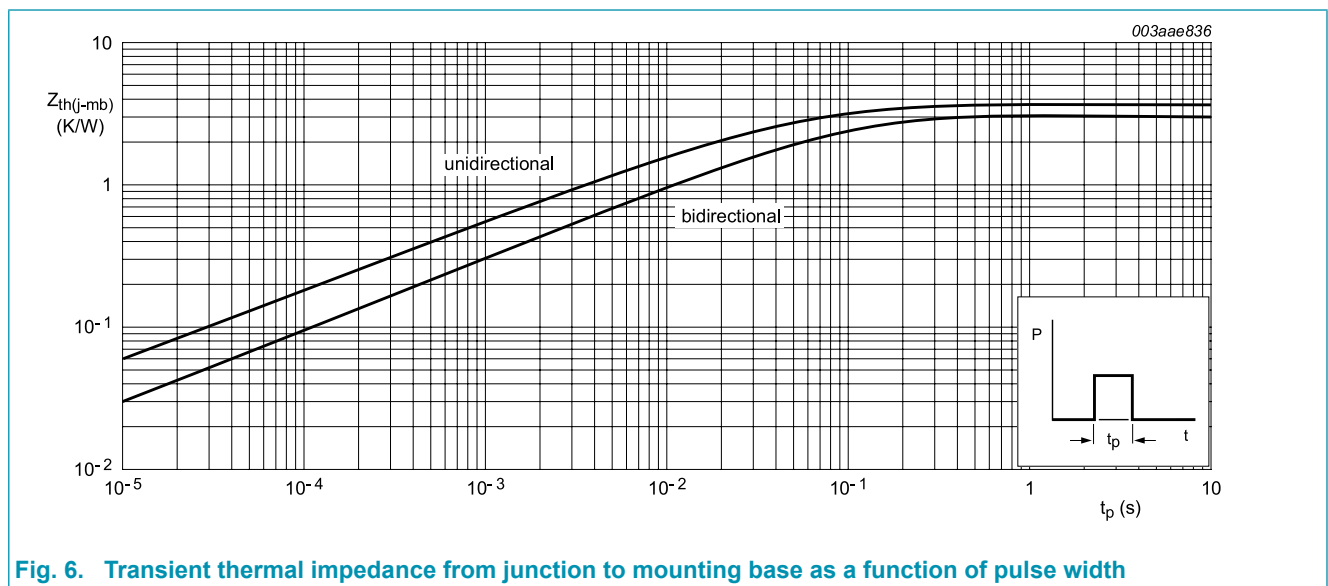
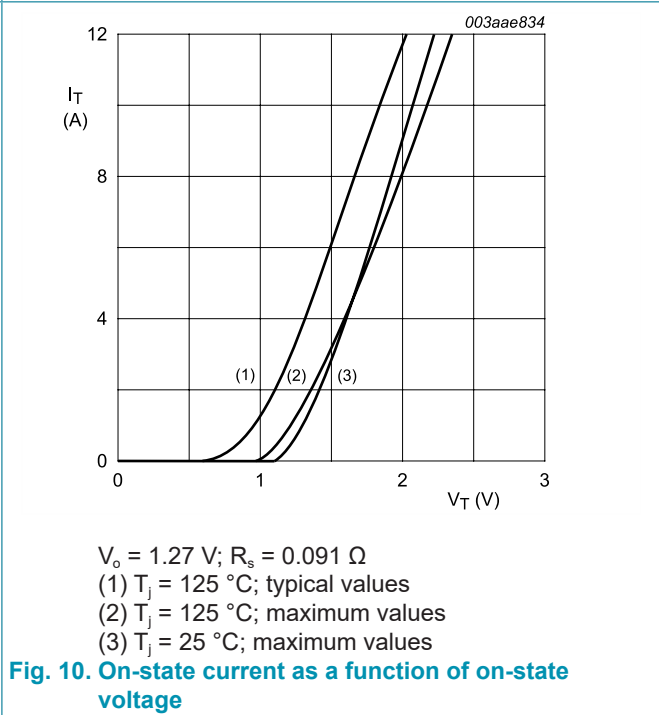
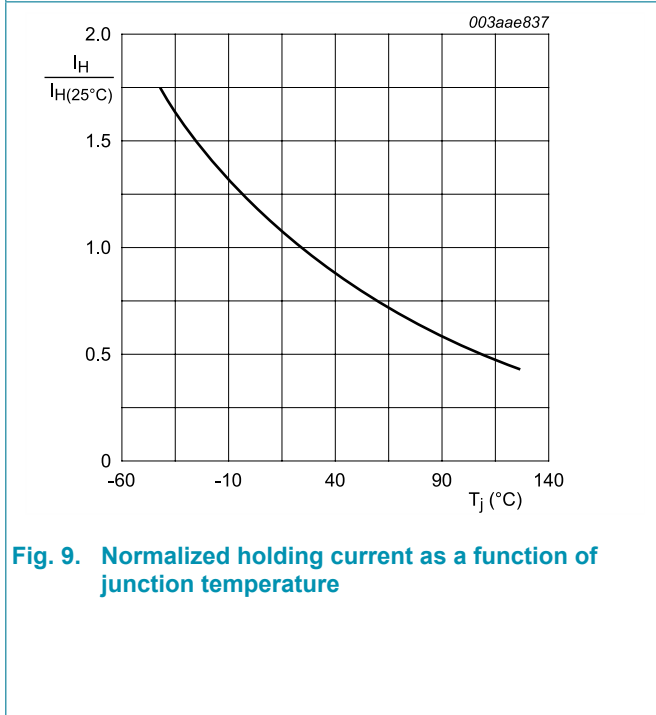
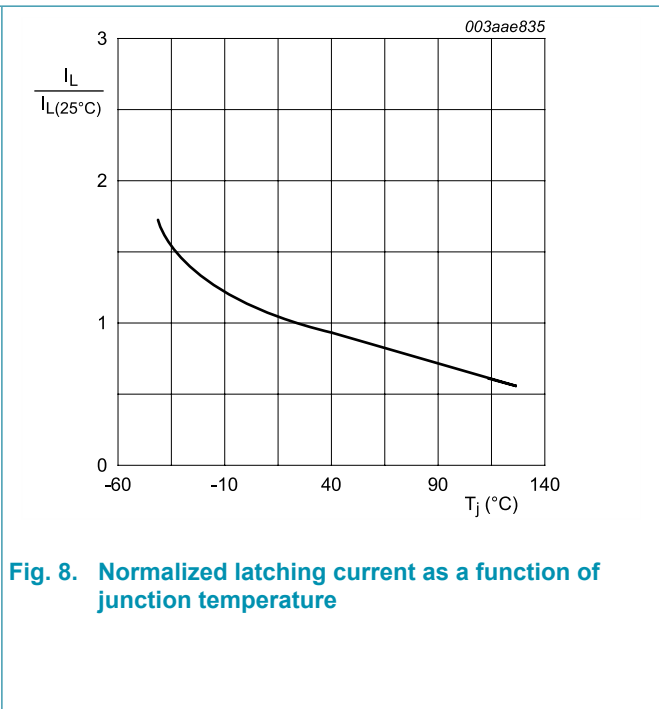
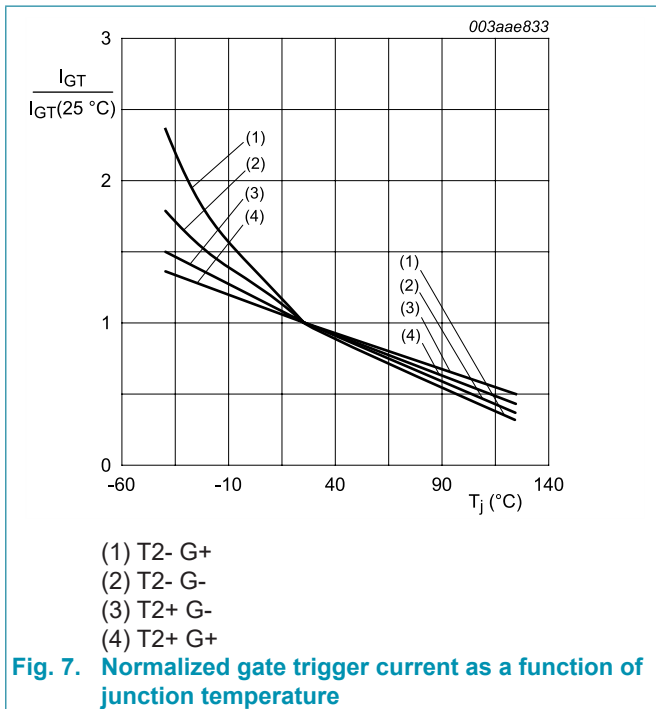


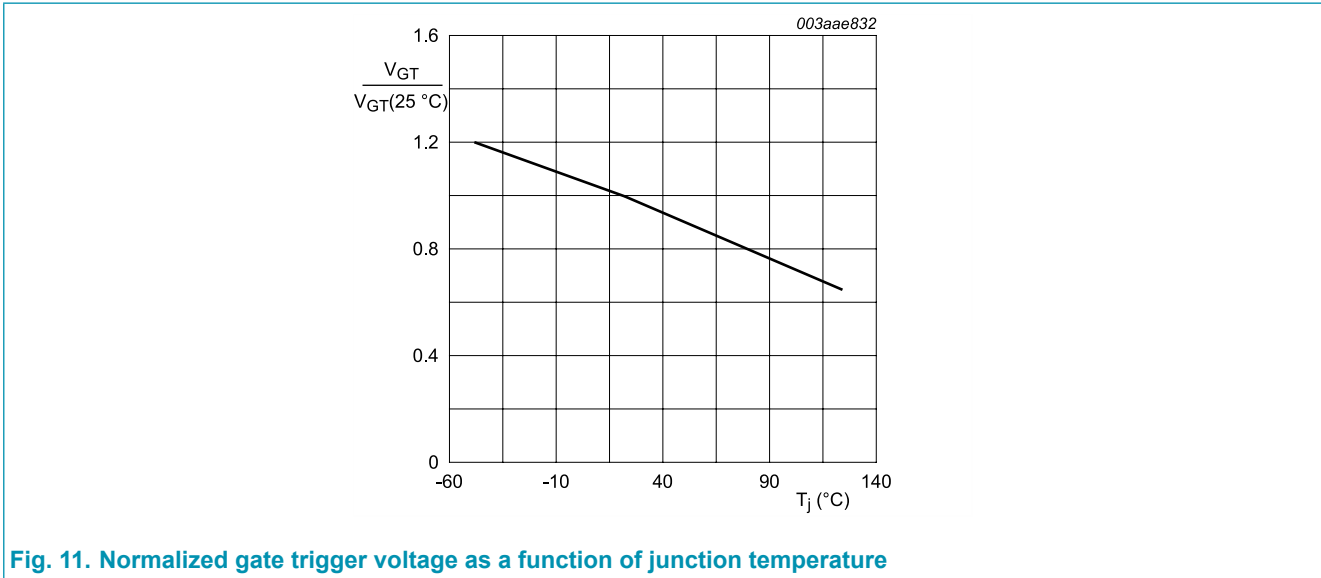
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	2	5	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	2.5	5	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	2.5	5	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	5	10	mA
I_L	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	1.6	10	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	4.5	15	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	1.2	10	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	2.2	15	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9	-	1.2	10	mA
V_T	on-state voltage	$I_T = 5\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 11	-	0.7	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 125\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$	-	5	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 6\text{ A}; V_D = 600\text{ V}; I_G = 0.1\text{ mA}; dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

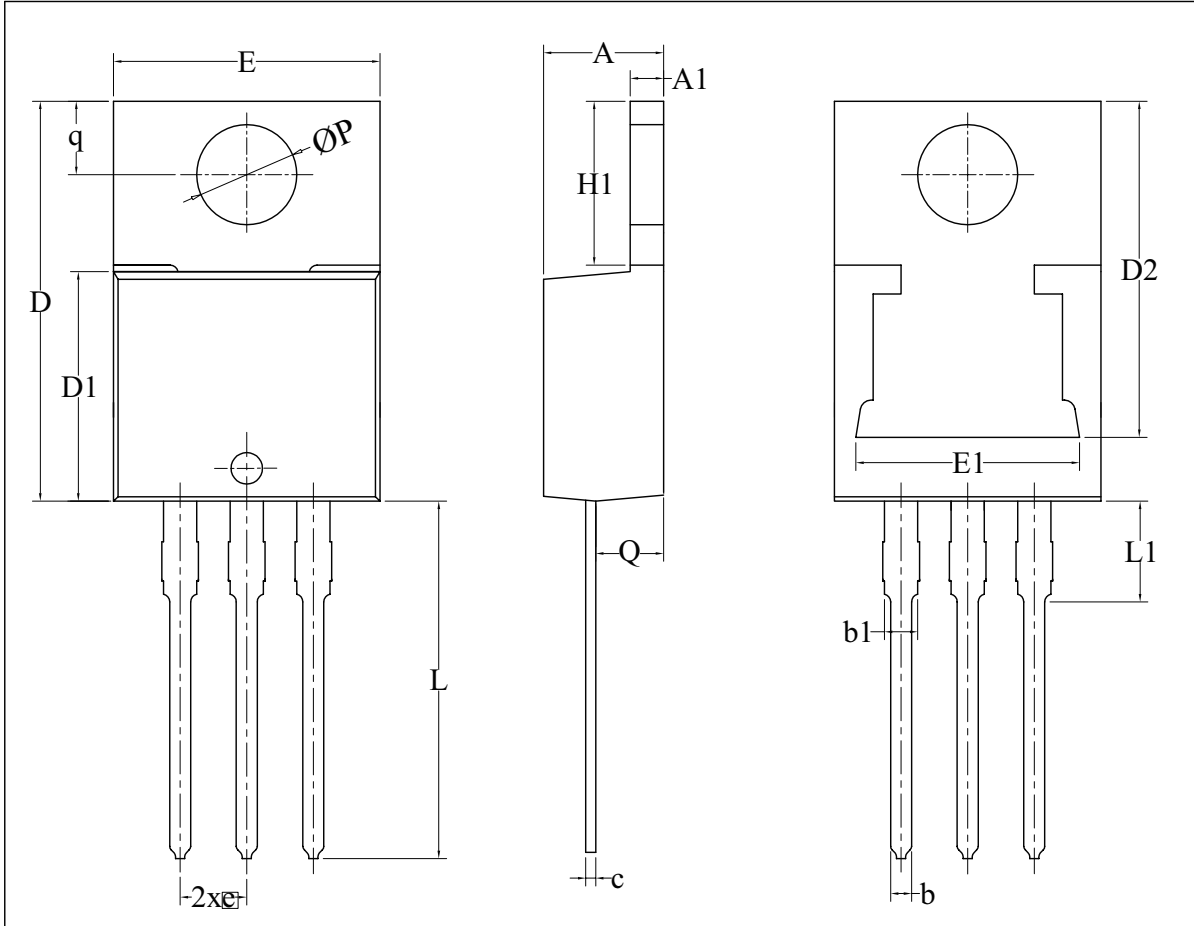




11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3 leads TO-220AB

TO220



Unit	A	A1	b	b1	c	D	D1	D2	E	E1	e	H1	L	L1	P	Q	q
MM	min	4.35	1.14	0.69	1.20	14.95	8.50	12.20	10.00	8.25	2.54 (BSC)	6.00	13.00	3.40	3.70	2.40	2.60
	max	4.75	1.40	1.01	1.45	15.55	9.02	12.88	10.40	8.89		6.40	14.00	3.80	3.95	2.80	3.00

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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